

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Withdrawn) A method for manufacturing a semiconductor device, comprising the steps of:

forming a first film pattern by discharging a conductive material with a droplet discharge method;

forming a first photosensitive material over the first film pattern;

forming a first mask pattern by irradiating a region where the first film pattern and the first photosensitive material are overlapped with a laser beam and by developing;

forming a gate electrode having a desired shape by etching the first film pattern using the first mask pattern as a mask;

forming an insulating film and a semiconductor film over the gate electrode;

forming a second photosensitive material over the semiconductor film;

forming a second mask pattern by irradiating the second photosensitive material with a laser beam and by developing;

forming a semiconductor region having a desired shape by etching the semiconductor film using the second mask pattern as a mask; and

forming a source electrode and a drain electrode to be in contact with the semiconductor region.

2. (Withdrawn) A method for manufacturing a semiconductor device, comprising the steps of:

forming a first film pattern by discharging a conductive material with a droplet discharge method;

discharging or applying a first photosensitive material over the first film pattern;

forming a first mask pattern by irradiating a region where the first film pattern and the first photosensitive material are overlapped with a laser beam and by developing;

forming a gate electrode having a desired shape by etching the first film pattern using a the first mask pattern as a mask;

forming an insulating film and a first semiconductor film over the gate electrode;

forming a protective film over the first semiconductor film;

forming a second semiconductor film over the first semiconductor film and the protective film;

forming a second photosensitive material over the second semiconductor film;

forming a second mask pattern by irradiating the second photosensitive material with a laser beam and by developing;

forming a semiconductor region having a desired shape by etching the first semiconductor film and the second semiconductor film using the second mask pattern as a mask; and

forming a source electrode and a drain electrode to be in contact with the semiconductor region.

3. (Original) A method for manufacturing a semiconductor device, comprising the steps of:

forming a first film pattern by discharging a conductive material with a droplet discharge method;

forming a first photosensitive material over the first film pattern;

forming a first mask pattern by irradiating a region where the first film pattern and the first photosensitive material are overlapped with a laser beam and by developing;

forming a source electrode and a drain electrode having a desired shape by etching the first film pattern using the first mask pattern as a mask;

forming a semiconductor film over the source electrode and the drain electrode;

forming a second photosensitive material over the semiconductor film;

forming a second mask pattern by irradiating the second photosensitive material with a laser beam and by developing;

forming a semiconductor region having a desired shape by etching the semiconductor film using the second mask pattern as a mask; and

forming an insulating film and a gate electrode over the semiconductor region.

4. (Original) A method for manufacturing a semiconductor device, according to any one of claims 1 to 3, wherein the first photosensitive material and the second photosensitive material are negative photosensitive resins.

5. (Original) A method for manufacturing a semiconductor device, according to any one of claims 1 to 3, wherein the first photosensitive material and the second photosensitive material are positive photosensitive resins.
6. (Original) A method for manufacturing a semiconductor device, according to any one of claims 1 to 3, wherein one of the first photosensitive material and the second photosensitive material is a negative photosensitive resin and the other is a positive photosensitive resin.
7. (Withdrawn) A method for manufacturing a television set, comprising the steps of:
 - forming a first film pattern by discharging a conductive material with a droplet discharge method;
 - forming a first photosensitive material over the first film pattern;
 - forming a first mask pattern by irradiating a region where the first film pattern and the first photosensitive material are overlapped with a laser beam and by developing,
 - forming a gate electrode having a desired shape by etching the first film pattern using the first mask pattern as a mask;
 - forming an insulating film and a semiconductor film over the gate electrode;
 - forming a second photosensitive material over the semiconductor film;
 - forming a second mask pattern by irradiating the second photosensitive material with a laser beam and by developing;
 - forming a semiconductor region having a desired shape by etching the semiconductor film using the second mask pattern as a mask;
 - forming a source electrode and a drain electrode to be in contact with the semiconductor region; and
 - forming a pixel electrode to be connected to the drain electrode.
8. (Withdrawn) A method for manufacturing a television set, comprising the steps of:
 - forming a first film pattern by discharging a conductive material with a droplet discharge method;
 - forming a first photosensitive material over the first film pattern;
 - forming a first mask pattern by irradiating a region where the first film pattern and the first photosensitive material are overlapped with a laser beam and by developing;

forming a gate electrode having a desired shape by etching the first film pattern using the first mask pattern as a mask;

forming an insulating film and a first semiconductor film over the gate electrode;

forming a protective film over the first semiconductor film;

forming a second semiconductor film over the first semiconductor film and the protective film;

forming a second photosensitive material over the second semiconductor film;

forming a second mask pattern by irradiating the second photosensitive material with a laser beam and by developing;

forming a semiconductor region having a desired shape by etching the first semiconductor film and the second semiconductor film using the second mask pattern as a mask;

forming a source electrode and a drain electrode to be in contact with the semiconductor region; and

forming a pixel electrode to be connected to the drain electrode.

9. (Original) A method for manufacturing a television set, comprising the steps of:

forming a first film pattern by discharging a conductive material with a droplet discharge method;

forming a first photosensitive material over the first film pattern;

forming a first mask pattern by irradiating a region where the first film pattern and the first photosensitive material are overlapped with a laser beam and by developing;

forming a source electrode and a drain electrode having a desired shape by etching the first film pattern using the first mask pattern as a mask;

forming a semiconductor film over the source electrode and the drain electrode;

forming a second photosensitive material over the semiconductor film;

forming a second mask pattern by irradiating the second photosensitive material with a laser beam and by developing;

forming a semiconductor region having a desired shape by etching the semiconductor film using the second mask pattern as a mask;

forming an insulating film and a gate electrode over the semiconductor region; and

forming a pixel electrode to be connected to the drain electrode.

10. (Original) A method for manufacturing a television set, according to any one of claims 7 to 9, wherein the first photosensitive material and the second photosensitive material are negative photosensitive resins.

11. (Original) A method for manufacturing a television set, according to any one of claims 7 to 9, wherein the first photosensitive material and the second photosensitive material are positive photosensitive resins.

12. (Original) A method for manufacturing a television set, according to any one of claims 7 to 9, wherein one of the first photosensitive material and the second photosensitive material is a negative photosensitive resin and the other is a positive photosensitive resin.

13. (Original) A method for manufacturing a semiconductor device, according to any one of claims 7 to 9, wherein the laser beam has any wavelength of from ultraviolet light to infrared light.

14. (Original) A method for manufacturing a television set, according to any one of claims 7 to 9, wherein the television set is a liquid crystal television or an EL television.

15. (Original) A method for manufacturing a semiconductor device, comprising the steps of:

- forming a first film pattern by a droplet discharge method;
- forming a photosensitive material over the first film pattern;
- forming a mask pattern by irradiating a region where the first film pattern and the photosensitive material are overlapped with a laser beam and by developing; and
- forming a second film pattern having a desired shape by etching the first film pattern using the mask pattern as a mask.

16. (Currently Amended) A method for manufacturing a semiconductor device according to claim [[1]] 15, further comprising the step of:

- forming a third film pattern to be connected to the second film pattern by a droplet discharge method.

17. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the photosensitive material is a negative photosensitive resin.
18. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the photosensitive material is a positive photosensitive resin.
19. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the first film pattern is a conductive film.
20. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the second film pattern is at least one of a gate electrode, a source electrode, or a drain electrode.
21. (Original) A method for manufacturing a semiconductor device according to claim 16, wherein the third film pattern is a wiring.
22. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the first film pattern is a semiconductor film.
23. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the second film pattern has a channel formation region, source region, or a drain region.
24. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the first film pattern is an insulating film.
25. (Original) A method for manufacturing a semiconductor device according to claim 15, wherein the second film pattern is an insulating film having an opening.
26. (Original) A method for manufacturing a semiconductor device, according to any one of claims 1, 2, 3, and 15, wherein the laser beam has any wavelength of from ultraviolet light to infrared light.

27. (Withdrawn) A semiconductor device comprising:
a wiring formed by a droplet discharge method; and
an electrode connected to the wiring,
wherein the wiring has a width of 5 μm or less.
28. (Withdrawn) A semiconductor device comprising:
a thin film transistor provided with a gate electrode, a gate insulating film, a
semiconductor region, a source electrode, and a drain electrode; and
a gate wiring connected to the gate electrode,
wherein the gate electrode has a width of 5 μm or less and the gate wiring is formed
by a droplet discharge method.
29. (Withdrawn) A television set comprising a display device including a wiring formed
by a droplet discharge method and an electrode connected to the wiring, wherein the
electrode has a width of 5 μm or less.
30. (Withdrawn) A television set comprising:
a display device including a thin film transistor with a gate electrode, a gate insulating
film, a semiconductor region, a source electrode, and a drain electrode; and
a gate wiring connected to the gate electrode,
wherein the gate electrode has a width of 5 μm or less and the gate wiring is formed
by a droplet discharge method.
31. (Withdrawn) A television set according to any one of claims 27 to 30, wherein the
television set is a liquid crystal television or an EL television.